

NITRIDE SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

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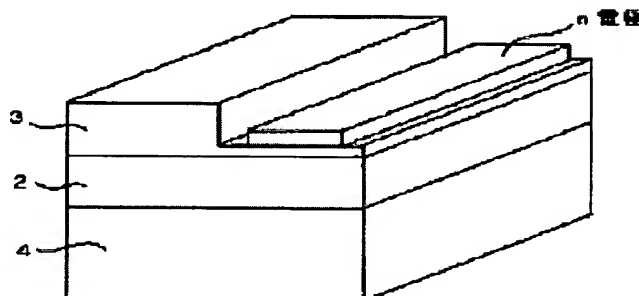
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Abstract of JP11214798

PROBLEM TO BE SOLVED: To provide a nitride semiconductor element of satisfactory heat dissipating properties and a manufacturing method thereof, wherein warpages, crackings and chippings are prevented from occurring in a GaN substrate, even if a sapphire substrate is removed, a wafer can be easily formed into chips, and the GaN substrate is protected against unnecessary cracking when it is cleaved.

SOLUTION: A GaN substrate 2 is formed on a first dissimilar substrate, the first dissimilar substrate is removed after or before an element structure 3 is laminated thereon, and a second dissimilar cleavable substrate 4 is bonded to the exposed part of the GaN substrate 2. Or the GaN substrate 2 is formed a thick as 80 μ m or above, the first dissimilar substrate is removed, the element structure 3 is formed on a surface located opposite to the exposed part, and the second dissimilar substrate 4 is not bonded.



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